

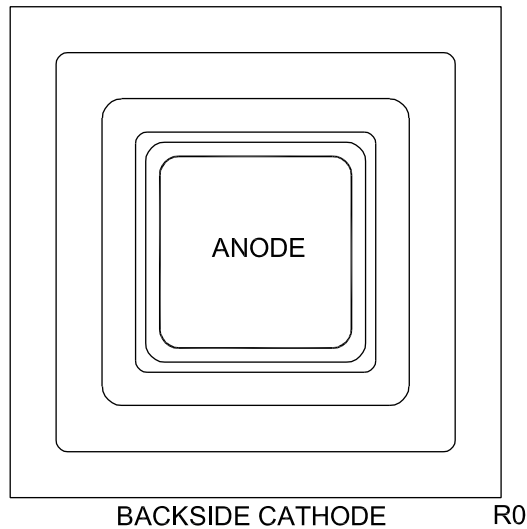
**PROCESS CPD93V**  
**Switching Diode**  
High Current Switching Diode Chip



**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	12.8 x 12.8 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	5.1 x 5.1 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 10,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

63,904

**PRINCIPAL DEVICE TYPES**

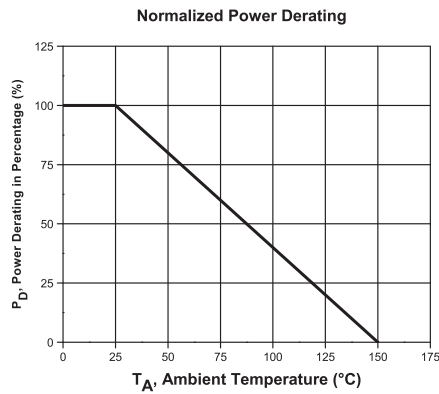
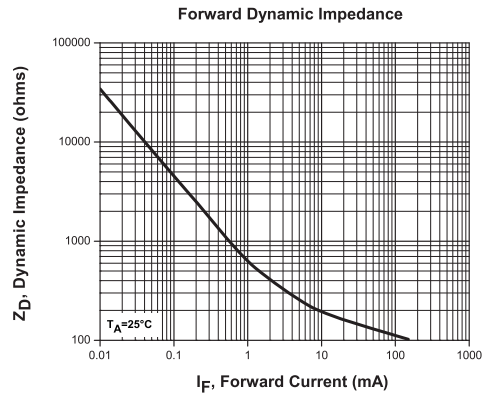
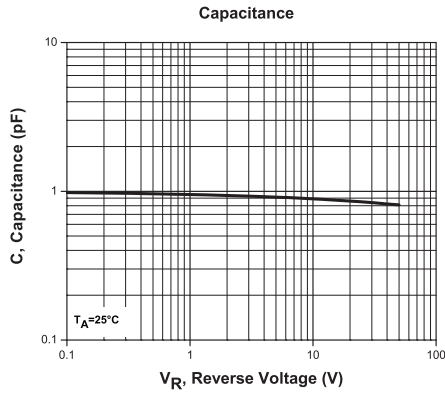
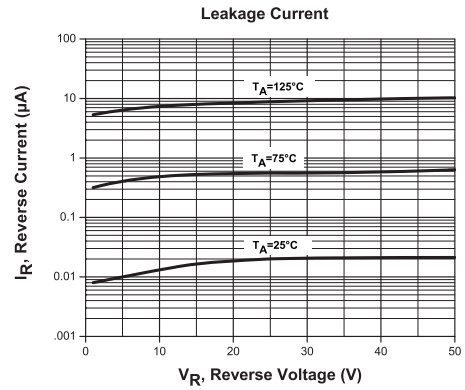
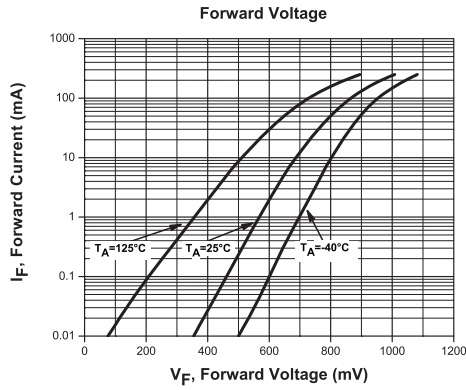
CMPD4150

BAS56

R2 (22-March 2010)

# PROCESS CPD93V

## Typical Electrical Characteristics



R2 (22-March 2010)